

C1 cont substrate 12, controlling the thickness of the LC layer 18, and suppressing disclination, so as to obtain an excellent image quality.

IN THE CLAIMS:

Please enter the following amended claims:

C2 10. (Amended) The method of claim 9, further comprising forming a film on said second substrate and patterning said film to form said black matrix.

11. (Amended) The method of claim 10, wherein said step of forming a film comprises forming a chrome film on said second substrate and patterning said chrome film to form said black matrix.

C3 16. (Amended) The method of claim 9, further comprising positioning a plurality of polarizing plates for sandwiching said first substrate and said second substrate between said polarizing plates.

C4 18. (Amended) The method of claim 9, wherein forming said gate insulating film comprises silicon oxide, an amorphous silicon layer and a N⁺ type amorphous silicon layer formed on said scanning lines and common electrodes.